N-Channel MOSFET

General Description

The WSR30N65CF uses advanced SGT MOSFET to provide excellent $R_{DS(ON)}$, low gate charge

This device is suitable for use as a Battery protection or in other Switching application.

Features

- 100% UIS + R_g Tested.
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- Moisture Sensitivity Level MSL1 (per JEDEC J-STD-020D)

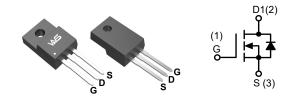
Product Summery

BV _{DSS}	R _{DS(ON)}	l _D
650V	0.125Ω	25A

Applications

 AC/DC Power Conversion in Switched mode Power Supplies (SMPS) .

TO-220F-3L Pin Configuration



Absolute Maximum Ratings (T_A=25°C, Unless Otherwise Noted)

Symbol	Parameter		Rating	Units	
V _{DS}	Drain-Source Voltage		650		
V _{GS}	Gate-Source Voltage	Gate-Source Voltage		V	
I _S	Diode Continuous Forward Current	T _C =25°C	25		
,	Continuous Dunin Courset	T _C =25°C	25	^	
I _D	Continuous Drain Current	T _C =100°C	19	Α	
I _{DM} ²	Pulse Drain Current	T _C =25°C	75		
Б	Maximum Power Dissipation	T _C =25°C	54	10/	
P _D		T _C =100°C	22	W	
R _{θJA} ⁴	Thermal Resistance-Junction to Ambient	Steady State	62.5	00000	
R _{θJC}	Thermal Resistance-Junction to Case		2.3	°C/W	
I _{AS} ³	Avalanche Current, Single pulse L=0.5mH		8.2	А	
E _{AS} ³	Avalanche Energy, Single pulse	L=0.5mH	336	mJ	
T _{STG}	Storage Temperature Range		-55 to 150	°0	
TJ	Maximum Junction Temperature		150	· °C	



N-Channel MOSFET

Electrical Characteristics (T_A=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Static Charac	Static Characteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250μA	650			V
7	Zoro Coto Voltago Proin Current	V _{DS} =520V , V _{GS} =0V			1.0	μΑ
I _{DSS}	Zero Gate Voltage Drain Current	T _J =85°C			30	
V _{GS(th)}	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_{DS}=250\mu A$	2.5	3.5	4.5	V
I _{GSS}	Gate Leakage Current	V_{GS} =±30V , V_{DS} =0V			±100	nA
R _{DS(ON)} ⁵	Drain-Source On-state Resistance	V_{GS} =10V , I_{D} =12A		0.125	0.15	Ω
Diode Charac	cteristics					
V _{SD} ⁵	Diode Forward Voltage	I _{SD} =25A , V _{GS} =0V		0.8	1.3	V
t _{rr}	Reverse Recovery Time	1 -12A di /dt-100A/		313		ns
Q _{rr}	Reverse Recovery Charge	- I _{DS} =12A , di _{SD} /dt=100A/μs		5.2		nC
Dynamic Cha	Dynamic Characteristics ⁶					
R_g	Gate Resistance	V _{GS} =0V , V _{DS} =0V , <i>f</i> =1.0MHz		3		Ω
C _{iss}	Input Capacitance	- V _{GS} =0V , V _{DS} =325V ,		2210	2890	
C _{oss}	Output Capacitance			55		pF
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz		5		
T _{d(on)}	Turn-on Delay Time			20		
T _r	Turn-on Rise Time	V_{DD} =30V , R_L =30 Ω , I_{DS} =1A ,		19		ns
T _{d(off)}	Turn-off Delay Time	V_{GEN} =10V , R_{G} =6 Ω		80		
T _f	Turn-off Fall Time			252		
Gate Charge	Gate Charge Characteristics ⁶					
Qg	Total Gate Charge			50		
Q _{gs}	Gate-Source Charge	V _{DS} =325V , V _{GS} =10V , I _{DS} =12/	٠	11		nC
$Q_{\rm gd}$	Gate-Drain Charge			19		

Note:

- 1. Calculated continuous current based on maximum allowable junction temperature. Bonding wire limitation current is 8A.
- 2. Pulse width limited by max. junction temperature.
- 3. UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_J =25°C).
- 4. Surface Mounted on 1in² pad area.
- 5. Pulse test ; pulse width≤300µs, duty cycle≤2%.
- 6. Guaranteed by design, not subject to production testing.



Typical Characteristics

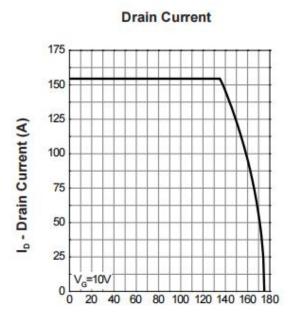
50

250 200 150 100

T_c - Case Temperature (°C)

Safe Operation Area

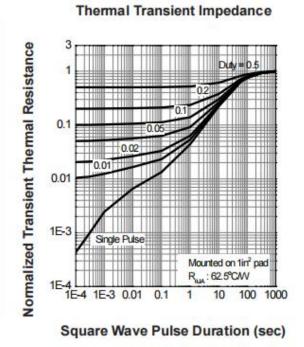
60 80 100 120 140 160 180



T_c - Case Temperature (°C)

300 100 10 RdslonLimit 10 ms 100ms 100ms 100ms 100ms 100ms 100ms 100ms 100c 1E-3 1E-4 1E-5 0.01 0.1 1 10 100 400

V_{DS} - Drain - Source Voltage (V)

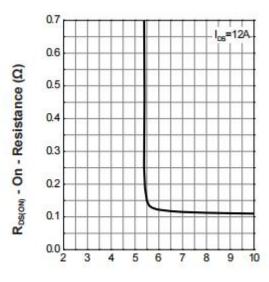


www.winsok.net Page 3 Rev 3.0: Jun. 2025



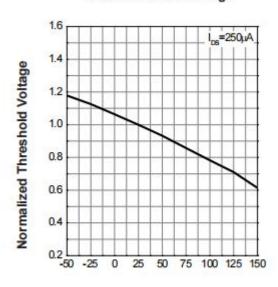
Typical Characteristics (Cont.)

Gate-Source On Resistance



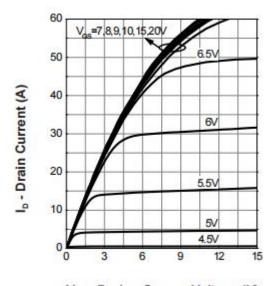
V_{GS} - Gate - Source Voltage (V)

Gate Threshold Voltage



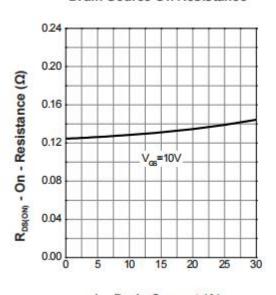
T_i - Junction Temperature (°C)

Output Characteristics



V_{DS} - Drain - Source Voltage (V)

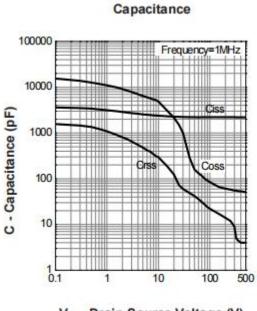
Drain-Source On Resistance



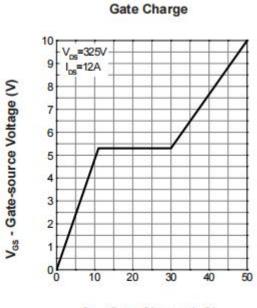
Ip - Drain Current (A)



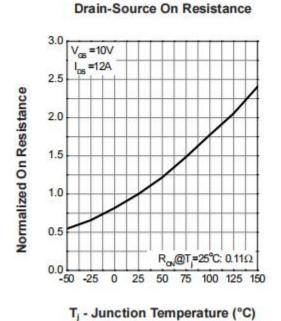
Typical Characteristics (Cont.)

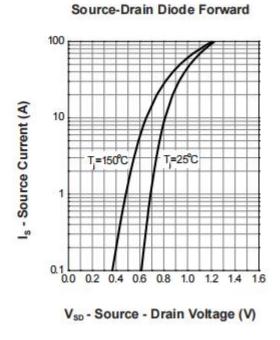


V_{DS} - Drain-Source Voltage (V)



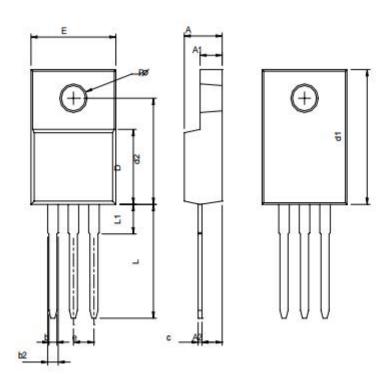
Q_G - Gate Charge (nC)





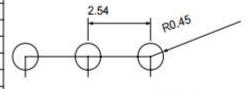


Packaging information



AP-SEROL	TO-220FP				
	MILLIMETERS		INCHES		
5	MIN.	MAX.	MIN.	MAX.	
A	4.20	4.80	0.165	0.189	
A1.	2.34	3.20	0.092	0.126	
A2	2.10	2.90	0.083	0.114	
b	0.50	0.90	0.020	0.035	
b2	0.91	1.90	0.035	0.075	
С	0.30	0.80	0.012	0.031	
D	8.10	9.40	0.319	0.370	
d1	14.50	16.50	0.571	0.650	
d2	12.10	12.90	0.476	0.508	
E	9.70	10.70	0.382	0.421	
e	2.54	BSC	0.100	BSC	
L	13.00	14.50	0.512	0.570	
L1	1.60	4.00	0.063	0.157	
P	3.00	3.60	0.118	0.142	

RECOMMENDED LAND PATTERN



UNIT: mm



N-Channel MOSFET

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